Abstract

Method for producing a semiconductor wafer composed of silicon with an epitaxially deposited layer

A method for producing a semiconductor wafer composed of silicon with an epitaxially deposited layer, comprising
placing a dummy wafer on a susceptor of an epitaxy reactor;
conducting an etching gas through the epitaxy reactor in order to remove residues on surfaces in the epitaxy reactor through the action of the etching gas;
conducting a first deposition gas through the epitaxy reactor in order to deposit silicon on surfaces in the epitaxy reactor;
replacing the dummy wafer by a substrate wafer composed of silicon; and
conducting a second deposition gas through the epitaxy reactor in order to deposit an epitaxial layer on the substrate wafer.

Fig. 4